

**isc Silicon NPN Power Transistor**
**BUW71**
**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 400V(\text{Min.})$
- Low Collector Saturation Voltage-  
:  $V_{CE(sat)} = 0.8V(\text{Max.}) @ I_C = 2A$
- High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

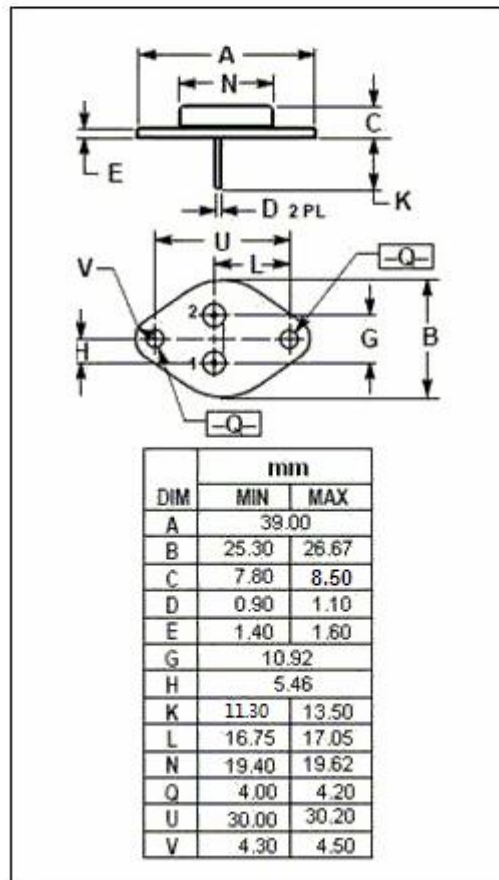
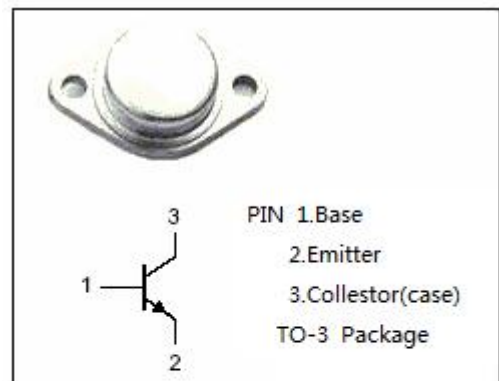
- Designed for use in clocked voltage converters.

**Absolute maximum ratings(Ta=25°C)**

| SYMBOL    | PARAMETER  | VALUE   | UNIT |
|-----------|--|---------|------|
| $V_{CBO}$ | Collector-Base Voltage                               | 450     | V    |
| $V_{CEO}$ | Collector-Emitter Voltage                            | 400     | V    |
| $V_{EBO}$ | Emitter-Base Voltage                                 | 7       | V    |
| $I_C$     | Collector Current-Continuous                         | 5       | A    |
| $I_B$     | Base Current-Continuous                              | 1.5     | A    |
| $P_C$     | Collector Power Dissipation<br>@T <sub>c</sub> =25°C | 100     | W    |
| $T_j$     | Junction Temperature                                 | 150     | °C   |
| $T_{stg}$ | Storage Temperature Range                            | -65~150 | °C   |

**THERMAL CHARACTERISTICS**

| SYMBOL        | PARAMETER                            | MAX  | UNIT |
|---------------|--------------------------------------|------|------|
| $R_{th\ j-c}$ | Thermal Resistance, Junction to Case | 1.25 | °C/W |



## isc Silicon NPN Power Transistor

## BUW71

## ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25°C unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS                                 | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| V <sub>(BR)CEO</sub> | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> = 10mA; I <sub>B</sub> = 0  | 400 |      |     | V    |
| V <sub>CE(sat)</sub> | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A |     |      | 0.8 | V    |
| V <sub>BE(sat)</sub> | Base-Emitter Saturation Voltage      | I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A |     |      | 1.5 | V    |
| I <sub>CBO</sub>     | Collector Cutoff Current             | V <sub>CB</sub> = 450V; I <sub>E</sub> = 0 |     |      | 0.1 | mA   |
| I <sub>EBO</sub>     | Emitter Cutoff Current               | V <sub>EB</sub> = 7V; I <sub>C</sub> = 0   |     |      | 0.1 | mA   |
| h <sub>FE</sub>      | DC Current Gain                      | I <sub>C</sub> = 2A; V <sub>CE</sub> = 5V  | 15  |      |     |      |

## Switching times

|                 |              |   |  |  |     |    |
|-----------------|--------------|---|--|--|-----|----|
| t <sub>on</sub> | Turn-on Time |   |  |  | 1.5 | μs |
| t <sub>s</sub>  | Storage Time | I <sub>C</sub> = 3A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.3A; R <sub>L</sub> = 20 Ω |  |  | 4.0 | μs |
| t <sub>f</sub>  | Fall Time    |   |  |  | 1.3 | μs |

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